TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCXH16374FT

Low-Voltage 16-Bit D-Type Flip-Flop with Bushold

The TC74VCXH16374FT is a high-performance CMOS 16-bit D-type flip-flop. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

This 16-bit D-type flip-flop is controlled by a clock input (CK) and an output enable input (\overline{OE}) which are common to each byte. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. When the \overline{OE} input is high, the outputs are in a high-impedance state.

The D data inputs include active bushold circuitry, eliminating the need for external pull-up resistors to hold unused or floating data inputs at a valid logic level.

All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation: V_{CC} = 1.8 to 3.6 V
- Bushold on data inputs eliminating the need for external pull-up/pull-down resistors
- High-speed operation: $t_{pd} = 3.0 \text{ ns} (\text{max}) (V_{CC} = 3.0 \text{ to } 3.6 \text{ V})$

$$t_{pd}$$
 = 3.9 ns (max) (V_{CC} = 2.3 to 2.7 V)

$$t_{pd} = 6.0 \text{ ns} (max) (V_{CC} = 1.8 \text{ V})$$

• Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA} \text{ (min)} (V_{CC} = 3.0 \text{ V})$

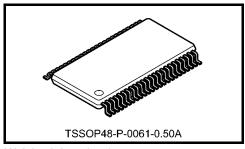
$$I_{OH}/I_{OL} = \pm 18 \text{ mA (min)} (V_{CC} = 2.3 \text{ V})$$

: $I_{OH}/I_{OL} = \pm 6 \text{ mA} \text{ (min)} (V_{CC} = 1.8 \text{ V})$

- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$

Human body model $\geq \pm 2000 \text{ V}$

- Package: TSSOP
- 3.6-V tolerant function and power-down protection control inputs and outputs



Weight: 0.25 g (typ.)

Pin Assignment (top view)

			1	
10E	1	\bigcirc	48	1CK
1Q1	2		47	1D1
1Q2	3		46	1D2
GND	4		45	GND
1Q3	5		44	1D3
1Q4	6		43	1D4
V _{CC}	7		42	V _{CC}
1Q5	8		41	1D5
1Q6	9		40	1D6
GND	10		39	GND
1Q7	11		38	1D7
1Q8	12		37	1D8
2Q1	13		36	2D1
2Q2	14		35	2D2
GND	15		34	GND
2Q3	16		33	2D3
2Q4	17		32	2D4
V _{CC}	18		31	V _{CC}
2Q5	19		30	2D5
2Q6	20		29	2D6
GND	21		28	GND
2Q7	22		27	2D7
2Q8	23		26	2D8
20E	24		25	2CK
		L	J	

IEC Logic Symbol

		r			
10E -	1 📐	1EN			
1CK	48	>C1			
20E -	24 📐	2EN			
20L 2CK-	25	>C2			
2010		Ľ.	_		
	47			2	
1D1 —	46	1D	1 🗸	3	- 1Q1
1D2 —	44			5	- 1Q2
1D3 —					- 1Q3
1D4 —	43			6	- 1Q4
1D5 —	41			8	- 1Q5
1D6 —	40			9	- 1Q6
1D7 —	38			11	- 1Q7
1D8 —	37			12	- 1Q8
2D1-	36	2D	2 🗸	13	- 2Q1
2D2	35		- •	14	- 2Q2
2D2 -	33			16	- 2Q3
2D3 2D4 —	32			17	- 2Q4
	30			19	
2D5 —	29			20	- 2Q5
2D6 -	27			22	- 2Q6
2D7 —	26	<u> </u>		23	- 2Q7
2D8 —					- 2Q8

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Truth Table

	Outputs		
1 0E	1CK	1D1-1D8	1Q1-1Q8
Н	Х	Х	Z
L		Х	Qn
L		L	L
L		Н	Н

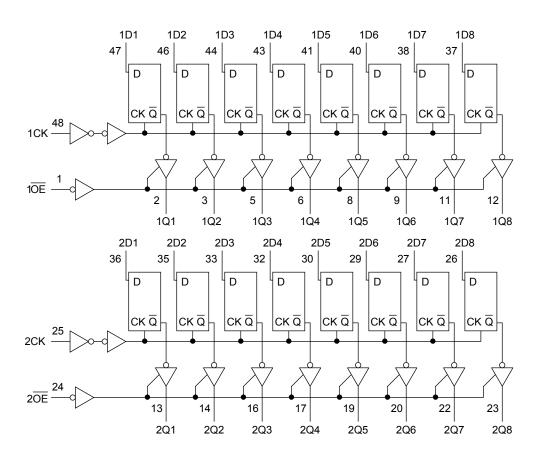
	Outputs		
20E	2CK	2D1-2D8	2Q1-2Q8
Н	Х	Х	Z
L		Х	Qn
L		L	L
L		Н	Н

X:	Don't	care

Z: High impedance

Qn: No change

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics		Symbol	Rating	Unit
Power supply voltage	Power supply voltage		-0.5 to 4.6	V
DC input voltage	(OE , CK)	V	-0.5 to 4.6	V
DC input voltage	(An)	V _{IN}	-0.5 to V _{CC} + 0.5	v
			-0.5 to 4.6 (Note 2)	
DC output voltage		VOUT	–0.5 to V _{CC} + 0.5	V
			(Note 3)	
Input diode current		lık	-50	mA
Output diode current		I _{OK}	±50 (Note 4)	mA
Output current		IOUT	±50	mA
Power dissipation		PD	400	mW
DC V _{CC} /ground current	t per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature		T _{stg}	–65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 2: OFF state
- Note 3: High or low state. IOUT absolute maximum rating must be observed.
- Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1) (Note 2)

Characteris	tics	Symbol	Rating	Unit	
Power supply voltage		Vcc	1.8 to 3.6	V	
		v.cc	1.2 to 3.6 (Note 3)	v	
Input voltage	(OE , CK)	Mar.	-0.3 to 3.6	V	
Input voltage	(An)	V _{IN}	0 to V _{CC}	v	
		Varia	0 to 3.6 (Note 4)	V	
Output voltage		Vout	0 to V _{CC} (Note 5)	v	
			±24 (Note 6)		
Output current		I _{OH} /I _{OL}	±18 (Note 7)	mA	
			±6 (Note 8)		
Operating temperature		T _{opr}	-40 to 85	°C	
Input rise and fall time		dt/dv	0 to 10 (Note 9)	ns/V	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: Floating or unused control inputs must be held high or low.

Note 3: Data retention

- Note 4: OFF state
- Note 5: High or low state
- Note 6: $V_{CC} = 3.0$ to 3.6 V
- Note 7: $V_{CC} = 2.3$ to 2.7 V
- Note 8: V_{CC} = 1.8 V
- Note 9: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V

Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characteris	stics	Symbol	Test C	Test Condition		Min	Max	Unit
	H-level	VIH	-			2.0		
Input voltage	L-level	VIL	-		2.7 to 3.6 2.7 to 3.6	_	0.8	V
			I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2			
	H-level	Voh	VIN = VIH or VII	I _{OH} = -12 mA	2.7	2.2	_	
		0.11		I _{OH} = -18 mA	3.0	2.4		
Output voltage				I _{OH} = -24 mA	3.0	2.2		V
				I _{OL} = 100 μA	2.7 to 3.6	_	0.2	
	I laval	N/	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 12 mA	2.7	_	0.4	
L-level	L-level	V _{OL}		I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage	(\overline{OE} , CK)	l	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	
current	(An)	l _{IN}	$V_{IN} = V_{CC}$ or GND		2.7 to 3.6	_	±5.0	μA
Bushold input minim	um drive	1	V _{IN} = 0.8 V		3.0	75	_	
hold current		II (HOLD)	V _{IN} = 2.0 V		3.0	-75	_	μA
Bushold input over-	drive current			(Note 1)	3.6		450	•
to change state		I _{I (OD)}	(Note 2)		3.6		-450	μA
3-state output OFF	state current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$		2.7 to 3.6		±10.0	μΑ
Power-off leakage c	urrent	IOFF	V _{OUT} = 0 to 3.6 V		0		10.0	μA
			$V_{IN} = V_{CC}$ or GND		2.7 to 3.6	_	20.0	
Quiescent supply cu	irrent	ICC	$V_{CC} \leq V_{OUT} \leq 3.6 \text{ V}$ (Note 3) 2.7		2.7 to 3.6	_	±20.0	μA
Increase in I _{CC} per i	input	Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6	_	750	μA

Note 1: An external driver must source at least the specified current to switch LOW-to-HIGH.

Note 2: An external driver must sink at least the specified current to switch HIGH-to-LOW.

Note 3: Outputs high impedance only.

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics		Symbol	Test C	condition		Min	Max	Unit
Characteria	5005	Symbol			V _{CC} (V)	IVIIII	IVIAX	Onic
Input voltage	H-level	VIH	-	—	2.3 to 2.7	1.6	_	V
input voltage	L-level	VIL	-		2.3 to 2.7	_	0.7	v
				I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2		
	H-level	Vон	VIN = VIH or VIL	I _{OH} = -6 mA	2.3	2.0	_	
				I _{OH} = -12 mA	2.3	1.8	_	
Output voltage				I _{OH} = -18 mA	2.3	1.7	_	V
			$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	2.3 to 2.7	_	0.2	
	L-level	V _{OL}		I _{OL} = 12 mA	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6	
Input leakage	(OE , CK)	l	V _{IN} = 0 to 3.6 V	-	2.3 to 2.7	_	±5.0	
current	(An)	lin	$V_{IN} = V_{CC} \text{ or } GND$		2.3 to 2.7	_	±5.0	μA
Bushold input minim	num drive		V _{IN} = 0.7 V		2.3	45	_	^
hold current		II (HOLD)	V _{IN} = 1.6 V		2.3	-45	_	μA
Bushold input over-	drive current			(Note 1)	2.7	_	300	^
to change state		I _{I (OD)}	(Note 2)		2.7	_	-300	μA
			$V_{IN} = V_{IH} \text{ or } V_{IL}$		0.040.07		10.0	^
3-state output OFF state current		I _{OZ}	V _{OUT} = 0 to 3.6 V		2.3 to 2.7	_	±10.0	μA
Power-off leakage of	urrent	I _{OFF}	V _{OUT} = 0 to 3.6 V		0		10.0	μA
	rrant	1	$V_{IN} = V_{CC}$ or GND		2.3 to 2.7	_	20.0	
Quiescent supply cu	literit	ICC	$V_{CC} \leq V_{OUT} \leq 3.6 \text{ V}$	(Note 3)	2.3 to 2.7	_	±20.0	μA

Note 1: An external driver must source at least the specified current to switch LOW-to-HIGH.

Note 2: An external driver must sink at least the specified current to switch HIGH-to-LOW.

Note 3: Outputs high impedance only.

DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	stics	Symbol	Test C	Test Condition		Min	Max	Unit
Input voltage	H-level	VIH	-	_	1.8 to 2.3	$0.7 \times V_{CC}$	_	V
input voltage	L-level	V _{IL}	-	_	1.8 to 2.3	_	$0.2 \times V_{CC}$	v
	H-level	Vон	H VIN = VIH OF VII	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage				I _{OH} = -6 mA	1.8	1.4	_	V
	L-level	Mai		I _{OL} = 100 μA	1.8		0.2	
	L-level	V _{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 6 mA	1.8	_	0.3	
Input leakage	(OE , CK)	lu i	V _{IN} = 0 to 3.6 V		1.8		±5.0	
current	(An)	l _{IN}	$V_{IN} = V_{CC}$ or GND		1.8	_	±5.0	μA
Bushold input minim	um drive		V _{IN} = 0.36 V		1.8	25	_	
hold current		II (HOLD)	V _{IN} = 1.26 V		1.8	-25	_	μA
Bushold input over-	drive current			(Note 1)	1.8	_	200	
to change state		I _{I (OD)}		(Note 2)	1.8	_	-200	μA
	toto ourrant	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$		1.0		10.0	
3-state output OFF s	3-state output OFF state current		V _{OUT} = 0 to 3.6 V		1.8	_	±10.0	μA
Power-off leakage c	urrent	I _{OFF}	$V_{OUT} = 0$ to 3.6 V		0	_	10.0	μA
	rront	laa	$V_{IN} = V_{CC}$ or GND		1.8		20.0	
Quiescent supply cu	Inent	Icc	$V_{CC} \leq V_{OUT} \leq 3.6 \text{ V}$	(Note 3)	1.8		±20.0	μA

Note 1: An external driver must source at least the specified current to switch LOW-to-HIGH.

Note 2: An external driver must sink at least the specified current to switch HIGH-to-LOW.

Note 3: Outputs high impedance only.

AC Characteristics (Ta = -40 to 85°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500 \Omega$) (Note 1)

Characteristics	Symbol	Test Condition		Min	Max	Unit
Characteristics	Symbol		$V_{CC}(V)$	IVIIII	Wax	Onic
			1.8	125	_	
Maximum clock frequency	f _{max}	Figure 1, Figure 2	2.5 ± 0.2	200	_	MHz
			3.3 ± 0.3	250		
Dropagation dalow time	•		1.8	1.5	6.0	
Propagation delay time (CK-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	1.0	3.9	ns
(UK-Q)	t _{pHL}		3.3 ± 0.3	0.8	3.0	
	+		1.8	1.5	7.0	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	1.0	4.6	ns
	^t pZH		$\textbf{3.3}\pm\textbf{0.3}$	0.8	3.5	
	t . –		1.8	1.5	5.0	
3-state output disable time	t _{pLZ} t _{pHZ}	Figure 1, Figure 3	2.5 ± 0.2	1.0	3.8	ns
			$\textbf{3.3}\pm\textbf{0.3}$	0.8	3.5	
Minimum pulse width	4	Figure 1, Figure 2	1.8	3.0		
(CK)	t _{w (H)}		2.5 ± 0.2	1.5		ns
	t _{w (L)}		$\textbf{3.3}\pm\textbf{0.3}$	1.5		
			1.8	2.5		
Minimum setup time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5		ns
			$\textbf{3.3}\pm\textbf{0.3}$	1.5		
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
	+		1.8	_	0.5	
Output to output skew	t _{osLH}	(Note 2)	2.5 ± 0.2	_	0.5	ns
	t _{osHL}		$\textbf{3.3}\pm\textbf{0.3}$	_	0.5	

Note 1: For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design. $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics

(Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	Test Condition			Тур.	Unit	
Characteristics	Symbol	rest condition		$V_{CC}(V)$	тур.	Offic	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	1.8	0.25		
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	2.5	0.6	V	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	0.8		
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	1.8	-0.25		
Quiet output minimum dynamic V _{OI}	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	2.5	-0.6	V	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	-0.8		
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	1.8	1.5		
Quiet output minimum dynamic V _{OH}	VOHV	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	2.5	1.9	V	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	2.2		

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

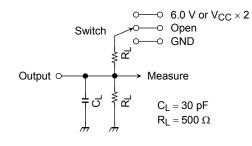
Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Output capacitance	CO		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Not	e) 1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation: $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16$ (per bit)

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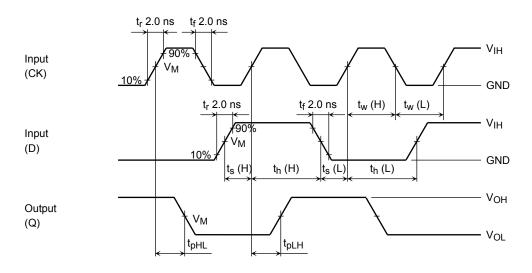
AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}			
t _{pHZ} , t _{pZH}	GND		

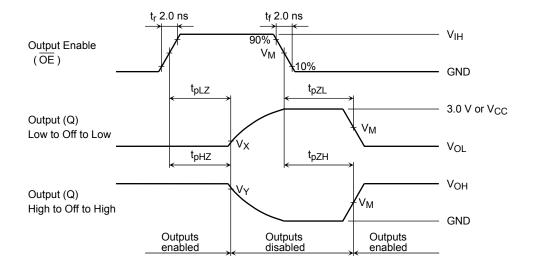
Figure 1

AC Waveform



 $\label{eq:Figure 2} \quad t_{pLH},\,t_{pHL},\,t_w,\,t_s,\,t_h$

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Symbol	V _{CC}				
Symbol	$3.3\pm0.3~V$	$2.5\pm0.2~\text{V}$	1.8 V		
VIH	2.7 V	V _{CC}	V _{CC}		
VM	1.5 V	V _{CC} /2	V _{CC} /2		
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V		
Vy	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V		

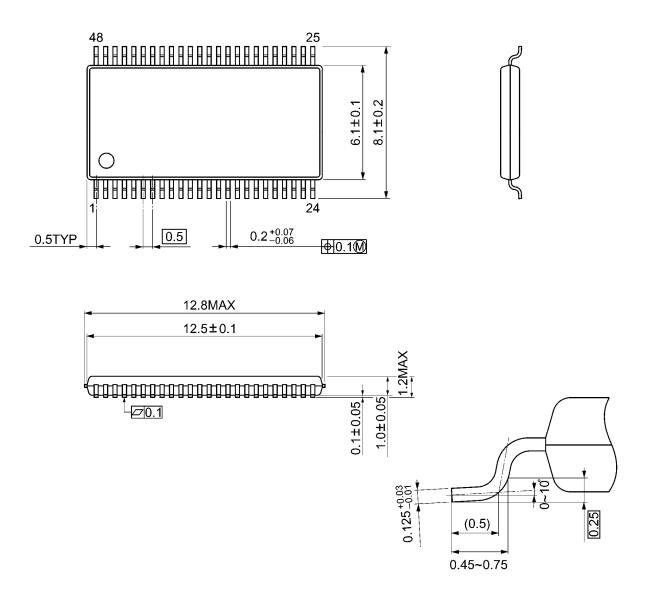
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}



Package Dimensions

TSSOP48-P-0061-0.50A

Unit: mm



Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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